Open up Future Electronics by Organic Molecules

Research Center of Integrative Molecular Systems
Division of Functional Molecular Systems

YAMAMOTO, Hiroshi
Professor
[yhiroshi@ims.ac.jp]

Education

1993	B.S. The University of Tokyo
1998	Ph.D. The University of Tokyo

Professional Employment

1998	Research Associate, Gakushuin University
1999	Special Postdoctral Fellow, RIKEN
2000	Research Scientist, RIKEN
2007	Senior Research Scientist, RIKEN
2012	Professor, Institute for Molecular Science Professor, The Graduate University for Advanced Studies
2012	Visiting Professor, Tokyo Institue of Technology
2015	Visiting Professor, Tohoku University

Awards

2009	RSC Publishing CrystEngComm Prize
2009	Young Scientist Awards, Japan Society for Molecular Science

Member

Assistant Professor
SUDA, Masayuki

Technical Associate
URUICHI, Mikio

Graduate Student
YANG, Fan*

Secretary
KAWAI, Shigeko

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Organic molecules are attracting recent attention as new ingredients of electronic circuits. Their functionalities have been developed considerably, but are still to be explored and advanced. Our group focuses on a development of organic electronics in the next era by providing new mechanism and concepts of the device operation and fabrication. For example, an electronic phase transition is utilized for the ON/OFF switching of our field-effect-transistor (FET). This special FET is called an organic Mott-FET, where the conduction electrons in the organic semiconductor are solidified at the OFF state because of Coulomb repulsion among carriers. However, these solidified electrons can be melted by applying a gate voltage, and show an insulator-to-metal transition so-called Mott-transition to be switched to the ON state. Because of this phase transition, a large response of the device can be achieved, resulting in the highest device mobility ever observed for organic FETs. At the same time, Mott-transition is known for its relevance to superconductivity. Not only in organic materials but also in inorganic materials such as cuprates, Mott-transition is frequently associated with superconducting phase at low temperature. Indeed, our organic FET shows an electric-field-induced superconducting transition at low temperature.

Another approach to the future electronics is a three-dimensional (3D) patterning of molecular devices using crystal engineering. Because each molecule can be designed to show different functionalities, it should be attractive to construct nano-structured devices by self-assembly. We are especially focusing on a development of supramolecular nanowires that allow 3D periodic wiring in nano-scale. By encapsulating a 1D array of conducting molecules in a channel formed inside 3D supramolecular network, it is possible to construct a sheathed nanowires aligned in a periodic order as shown in Figure 1.

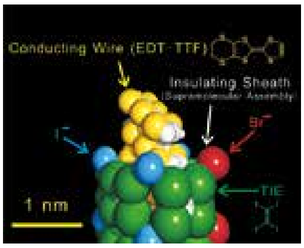

Figure 1. Crystal structure of supramolecular nanowire.

Selected Publications

- M. Suda, R. Kato and H. M. Yamamoto, "Light-Induced Superconductivity Using a Photo-Active Electric Double Layer," *Science* **347**, 743–746 (2015).
- H. M. Yamamoto, M. Nakano, M. Suda, Y. Iwasa, M. Kawasaki and R. Kato, "A Strained Organic Field-Effect Transistor with a Gate-Tunable Superconducting Channel," *Nat. Commun.* **4**, 2379 (7 pages) (2013).
- H. M. Yamamoto, "Sheathed Nanowires Aligned by Crystallographic Periodicity: A Possibility of Cross-Bar Wiring in Three-Dimensional Space," *CrystEngComm* **16**, 2857–2868 (2014).
- Y. Kawasugi, H. M. Yamamoto, N. Tajima, T. Fukunaga, K. Tsukagoshi and R. Kato, "Field-Induced Carrier Delocalization in the Strain-Induced Mott Insulating State of an Organic Superconductor," *Phys. Rev. Lett.* **103**, 116801 (4 pages) (2009).

1. Light-Induced Superconductivity in an Organic Mott-FET[1)]

κ-(BEDT-TTF)Cu[N(CN)$_2$]Br (κ-Br) is an organic Mott-insulator at room-temperature, but turns into metallic and superconducting states at low temperature. In our previous works, a tensile strain from FET substrate altered its ground state into a Mott-insulating state, when its thin (100–300 nm) crystal was laminated on top of SiO$_2$/Si^{++} substrate and cooled down to low temperature. In those experiments the electronic state became completely insulating because of the tensile strain that originates in mismatching of thermal expansion coefficients between κ-Br (30 ppm/K) and Si substrate (2 ppm/K). However, one can anticipate from the *T–P* (temperature *vs*. pressure) phase diagram that mixed electronic state between superconducting and Mott-insulating states can be realized when the tensile strain is much weaker. To achieve such a mixed state (or, percolate-superconducting state), Nb-doped SrTiO$_3$ is used as a back-gate substrate because of its larger thermal expansion coefficient (*ca.* 10 ppm/K) than Si. An aluminum oxide layer was grown by atomic layer deposition technique to form a gate dielectric on the substrate to form a FET device structure. Moreover, we have covered this oxide layer with photochromic self-assembled monolayer (SAM-layer: Figure 2, right panel) in order to make it photo-active.

Upon irradiation of UV-light, the resistivity at 2 K goes down quickly and low-resistance state was observed after 180 sec. By performing resistance measurement with sweeping temperature, it turned out that Mott-insulating part of the device became superconducting by the above UV-light irradiation, which was confirmed by a sudden drop of resistivity around 7 K. This is because of the hole-doping at the FET interface that is induced by strong internal dipole moment of the SAM-layer. This mechanism was also confirmed by dual-gate action of this device, where gate-induced carriers worked cooperatively with the photo-induced carriers. This result is the first example of light-induced superconductivity in FET devices, and allows remote control of superconducting device without direct wiring.

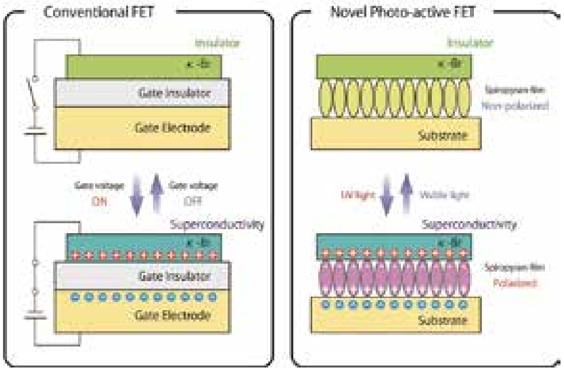

Figure 2. Device schematic for conventional superconducting FET (left) and our photo-active FET (right).

2. Strain-Tunable Organic FET with Strongly Correlated Electron Systems[2)]

Organic materials are soft and can be stretched even at low temperature. Our organic Mott-FETs are also soft enough to be compressed or expanded with a plastic substrate and show a band-width-controlled Mott/superconducting transitions. This kind of lattice modulation has been demonstrated in our recent experiments by mechanically pushing a poly-ethylene naphthalate (PEN) substrate covered with gold gate electrode and parylene-C dielectric from the back side (Figure 3). The organic Mott-insulator κ-(BEDT-TTF)Cu[N(CN)$_2$]Cl (κ-Cl) laminated on top of the substrate exhibited superconductor-to-insulator transition by bending the substrate where the surface has an effect of tensile strain in a longitudinal direction. The strain necessary for this transition at 5 K is only 0.3% while the resistance change reached ten orders of magnitude, which demonstrates high sensitivity of the Mott-insulator. The phase diagram obtained by simultaneous scans of strain and temperature well reproduces that of hydrostatic pressure. This means that one-dimensional tensile strain corresponds to an effective negative pressure in κ-Cl system.

Then, a field-effect was examined by applying a gate electric field. The transfer characteristics at higher tensile strain showed only moderate device mobility of around 5 cm^2/Vs. When the system was forced to stay in a mixed phase state, where superconducting and Mott-insulating phases coexist, the electric-field-effect maximized to show device mobility up to 5900 cm^2/Vs. This high response of the device can be attributed to an increase of superconducting fraction at application of gate voltage. In order to examine the above hypothesis, we have applied a magnetic field up to 7 T. Indeed, the field-effect has been considerably suppressed because the superconducting phases are destroyed by the magnetic field. This electric-field-induced superconductivity seems to originate from a decrease of Coulomb repulsion among carriers by electrostatic doping effect.

(BEDT-TTF = bis(ethyelenedithio)tetrathiafulvalene)

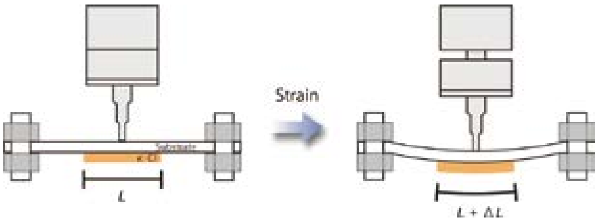

Figure 3. Side-view schematic for flexible organic Mott-FET device.

References

1) M. Suda, R. Kato and H. M. Yamamoto, *Science* **347**, 743–746 (2015).

2) M. Suda, Y. Kawasugi, T. Minari, K. Tsukagoshi, R. Kato and H. M. Yamamoto, *Adv. Mater.* **26**, 3490–3495 (2014).

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* carrying out graduate research on Cooperative Education Program of IMS with Tokyo Institute of Technology